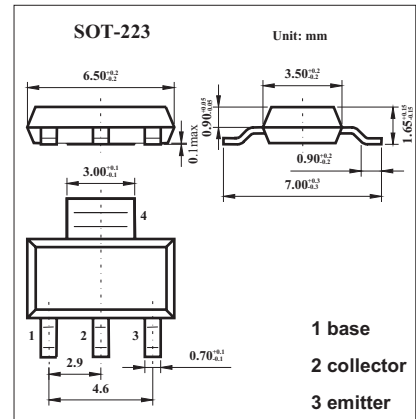


■ Features

- 60 Volt  $V_{CE0}$ .
- 3 Amp continuous current.
- Low saturation voltage.



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-80	V
Collector-emitter voltage	$V_{CEO}$	-60	V
Emitter-base voltage	$V_{EBO}$	-5	V
Continuous collector current	$I_{CM}$	-6	A
Peak pulse current	$I_C$	-3	A
Power dissipation	$P_{tot}$	2	W
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	$^\circ\text{C}$

■ **Electrical Characteristics** Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100μA	-80			V
Collector-emitter breakdown voltage *	V(BR)CEO	IC=-10mA	-60			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA	-5			V
Collector Cut-Off Current	ICBO	VCB=-60V VCB=-60V, Ta = 100°C			-0.1 -10	μA
Emitter Cut-Off Current	IEBO	VEB=-4V			-0.1	μA
Collector-emitter saturation voltage *	VCE(sat)	IC=-1A, IB=-100mA IC=-3A, IB=-300mA		-0.15 -0.45	-0.3 -0.6	V
Base-emitter saturation voltage *	VBE(sat)	IC=-1A, IB=-100mA		-0.9	-1.25	V
Base-emitter ON voltage *	VBE(on)	IC=-1A, VCE=-2V		-0.8	-1.0	V
Collector Cut-Off Current Transfer Ratio *	hFE	IC=-50mA, VCE =-2V*	70	200		
		IC=-500mA, VCE =-2V*	100	200	300	
		IC=-1A, VCE =-2V*	80	170		
		IC=-2A, VCE =-2V*	40	150		
Transitional frequency	fT	IC=-100mA, VCE=-5V, f=100MHz	100	140		MHz
Output capacitance	Cobo	VCB=-10V, f=1MHz			30	pF
Turn-on time	t(on)	IC=-500mA, VCC=-10V		40		ns
Turn-off time	t(off)	IB1=IB2=-50mA		450		ns

\* Pulse test: tp = 300 μs; d ≤ 0.02.

■ **Marking**

Marking	FZT751
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